

Atty. Dkt. No. 039153-0363 (F0804)

**Amendments to the Specification:**

Please amend the specification as follows:

Please replace paragraph number [0013], with the following rewritten paragraph:

[0013] Still another exemplary embodiment relates to a method of manufacturing an ultra-large scale integrated circuit. The integrated circuit includes a transistor with a T-shaped conductor. The method includes steps of providing a first layer above a substrate, providing an oxide layer on the first layer, forming a first trench in the oxide layer, forming a second trench in the first layer, and providing a gate conductor material in the first trench and the second trench to form the T-shaped conductor. The first layer is a silicon rich nitride layer or a silicon oxynitride layer. The second trench has a smaller width than the first trench.